

DATASHEET

Opto Interrupter ITR9909

Features

- Fast response time
- High analytic
- Cut-off visible wavelength λp=940nm
- High sensitivity
- Pb free
- This product itself will remain within RoHS compliant version

Description

- The ITR9909 consist of an infrared emitting diode and an NPN silicon phototransistor, encased side-by-side on converging optical axis in a black thermoplastic housing,
- The phototransistor receives radiation from the IR only .This is the normal situation.
- But when an object is in between , phototransistor could not receives the radiation.
- For additional component information , please refer to IR and PT

Applications

- Mouse Copier
- Switch Scanner
- Floppy disk driver
- Non-contact Switching
- For Direct Board

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Device Selection Guide

Device No.	Chip Materials	Lens Color		
IR	GaAlAs	Blue		
PT	Silicon	Black		

Absolute Maximum Ratings (Ta=25)

Parameter		Symbol	Ratings	Unit
IIIput	Power Dissipation at(or below) 25 Free Air Temperature	Pd	75	mW
	Reverse Voltage	V_R	5	V
	Forward Current	I _F	50	mA
	Peak Forward Current (*1) Pulse width 100µs, Duty cycle=1%	I _{FP}	1	А
Output	Collector Power Dissipation	Pd	75	mW
	Collector Current	Ic	50	mA
	Collector-Emitter Voltage	B V _{CEO}	30	V
	Emitter-Collector Voltage	B V _{ECO}	5	V
Operating Temperature		Topr	-25~+85	
Storage Temperature		Tstg	-40~+85	
Lead Soldering Temperature (*2) (1/16 inch form body for 5 seconds)		Tsol	260	

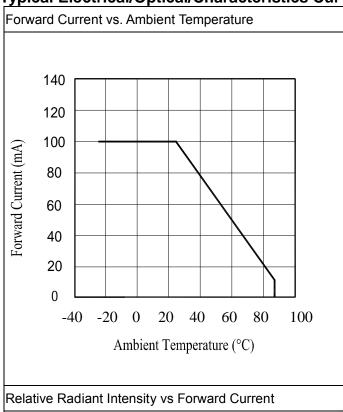
(*1) $tw=100 \mu sec.$, T=10 msec. (*2) t=5 Sec

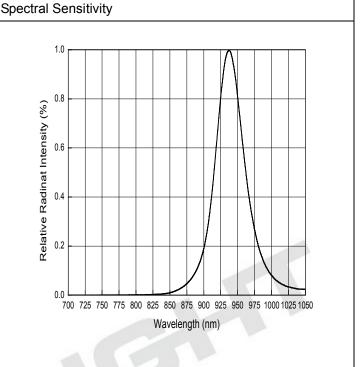


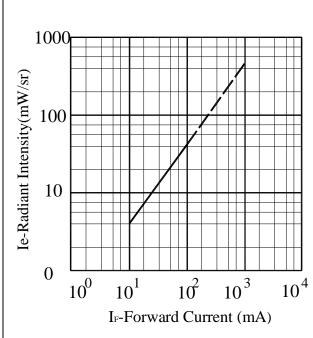
Electro-Optical Characteristics (Ta=25)

Parameter		Symbol	Min.	Тур.	Max.	Unit	Conditions		
Input	Forward Voltage	VF		1.2	1.5	V	I _F =20mA		
				1.4	1.85		IF=100mA, tp=100 μ s,tp/T=0.01		
				2.6	4.0		IF=1A,tp=100 μ s,tp/T=0.01		
	Reverse Current	I _R			10	μΑ	V _R =5V		
	Peak Wavelength	λ_{P}		940		nm	I _F =20mA		
Output	Dark C urrent	I _{CEO}			100	nA	V _{CE} =20V,Ee=0mW/cm ²		
	C-E Saturation Voltage	V _{CE} (sat)			0.4	V	I _C =2mA Ee=1mW/cm ²		
Transfer Characteristics	Collect Current	I _C (ON)	200			uA	V _{CE} =5V IF=20mA		
	Rise time	t _r		15		µsec	V_{CE} =5V, I_{C} =1mA , R_{L} =1000 Ω		
	Fall time	t _f		15		µsec			

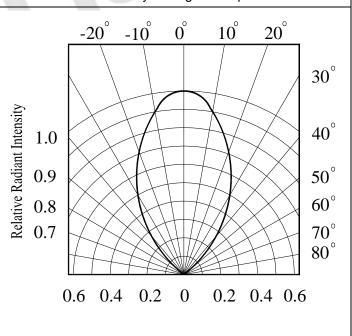
Typical Electrical/Optical/Characteristics Curves for IR



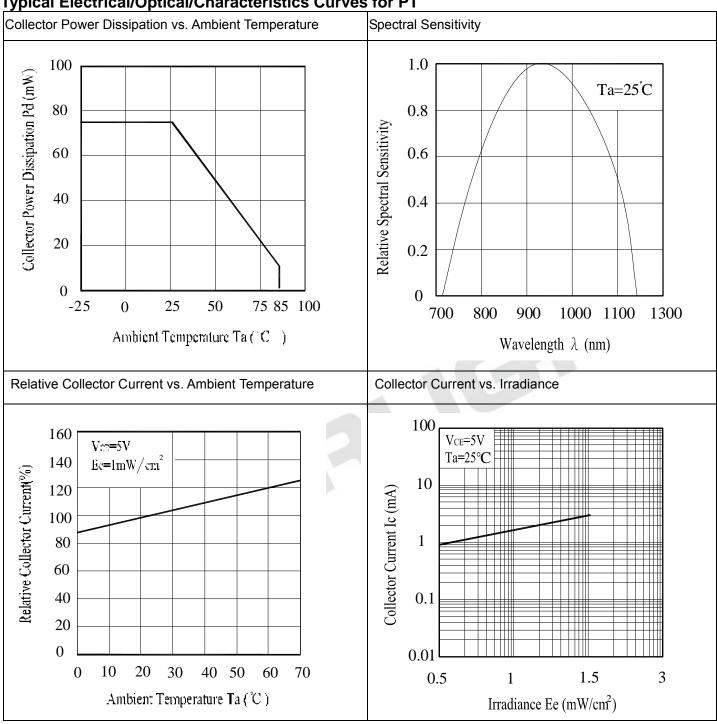


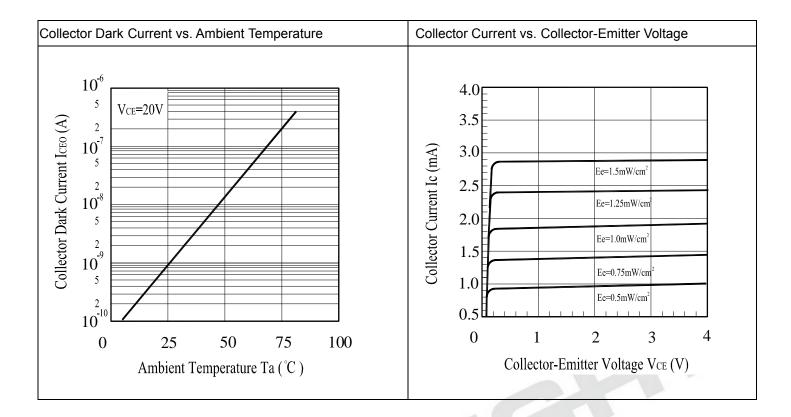


Relative Radiant Intensity vs Angular Displacement

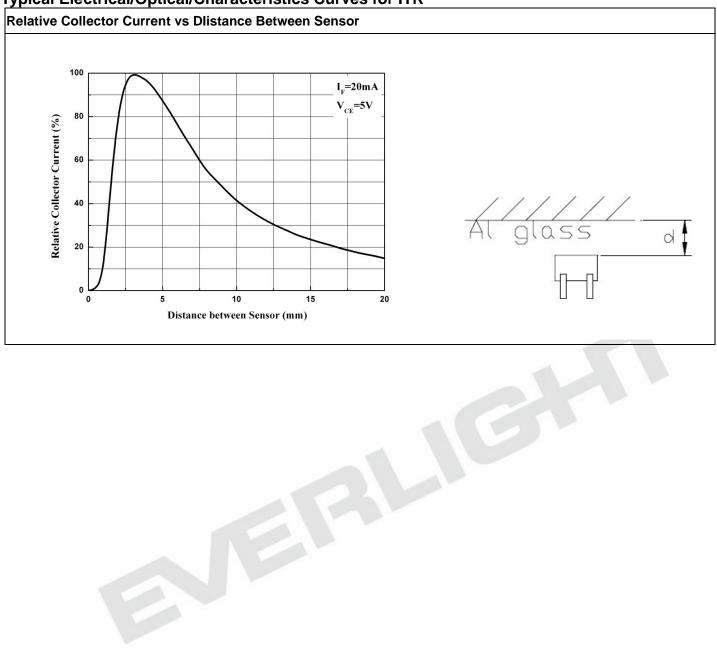


Typical Electrical/Optical/Characteristics Curves for PT



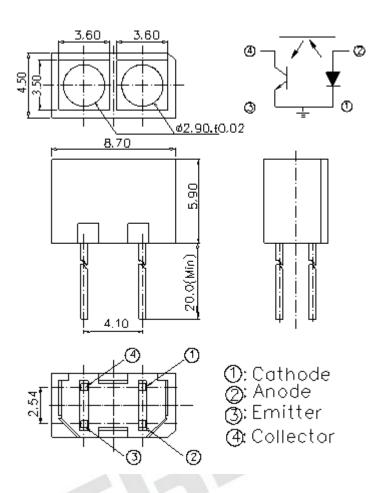


Typical Electrical/Optical/Characteristics Curves for ITR





Package Dimension



Note: Tolerances unless dimensions ±0.25mm

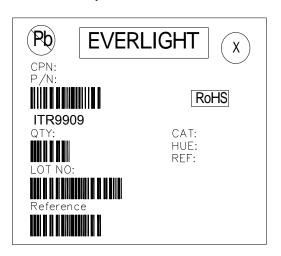


Packing Quantity Specification

1.150PCS/1 Bag, 5 Bags/1Box

2. 10Boxes/1Carton

Label Form Specification



- · CPN: Customer's Product Number
- P/N: Product Number
- QTY: Packing Quantity
- CAT: Luminous Intensity Rank
- HUE: Dom. Wavelength Rank
- REF: Forward Voltage RankLOT No: Lot Number
- X: Month
- Reference: Identify Label Number

Notes

- 1. Above specification may be changed without notice. EVERLIGHT will reserve authority on material change for above specification.
- 2. When using this product, please observe the absolute maximum ratings and the instruction for using outlined in these specification sheets. EVERLIGHT assumes no responsibility for any damage resulting from use of the product which does not comply with the absolute maximum ratings and the instructions included in these specification sheets.
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